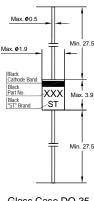
SILICON SCHOTTKY BARRIER DIODES

for general purpose applications

The SD103A, B, C is a metal on silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications. Other uses are for click suppression, efficient full wave bridges in telephone subsets, and as blocking diodes in rechargeable low voltage battery system.

This diode is also available in MiniMELF case with type designation LL103A, B, C.



Glass Case DO-35 Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit	
Peak Reverse Voltage	SD103A SD103B SD103C	V_{RRM}	40 30 20	V	
Power Dissipation		P _{tot}	400 1)	mW	
Single Cycle Surge 60 Hz Sine Wave		I _{FSM}	15	А	
Junction Temperature		T _j	125	°C	
Storage Temperature Range		Ts	- 55 to + 175	°C	
1) Valid provided the leads direct at the case ar	re kept at ambie				

Characteristics at T_a = 25 °C

Parameter		Symbol	Тур.	Max.	Unit
Forward Voltage at $I_F = 20 \text{ mA}$ at $I_F = 200 \text{ mA}$		V_{F}		0.37 0.6	V
at $V_R = 20 \text{ V}$	SD103A SD103B SD103C	I _R	-	5	μΑ
Junction Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$		C_tot	50	-	pF
Reverse Recovery Time at $I_F = I_R = 5$ mA to 200 mA, recover to 0.1 I_R		t _{rr}	10	-	ns

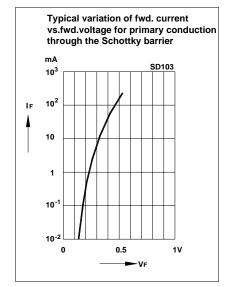


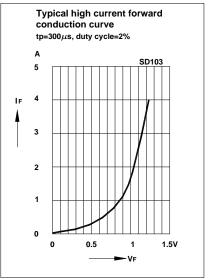


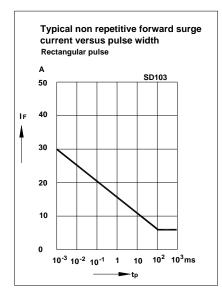


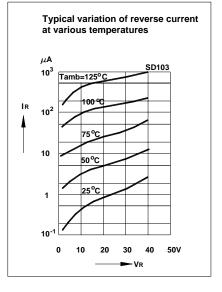


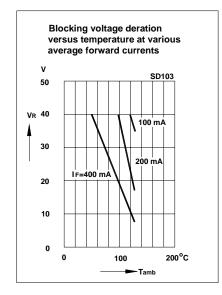
SEMTECH ELECTRONICS LTD.

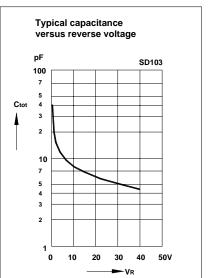














SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)





